

ABSTRACT OF THE DISCLOSURE

A method of fabricating a thin film transistor by setting the temperature of a heat treatment for crystallizing an active layer which is formed on a substrate at a level not deforming the substrate and activating an impurity layer in a heat treatment method different from that employed for the heat treatment, and a semiconductor device prepared by forming a heat absorption film, a semiconductor film, a gate insulating film, and a gate electrode on a substrate, the heat absorption film being provided within a region substantially corresponding to the semiconductor film.